

**DESCRIPTION**

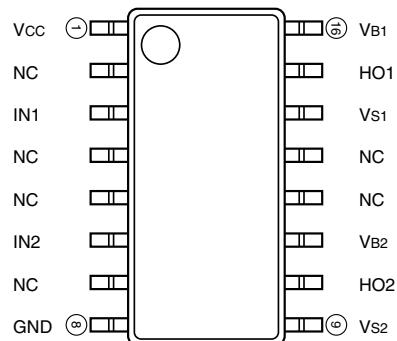
M81731FP is high voltage Power MOSFET and IGBT module driver for half bridge applications.

**FEATURES**

- FLOWING SUPPLY VOLTAGE ..... 600V
- OUTPUT CURRENT .....  $\pm 3A$  (typ)
- UNDERRATE VOLTAGE LOCKOUT
- BUILT-IN INPUT NOISE FILTER
- SOP-16 PACKAGE

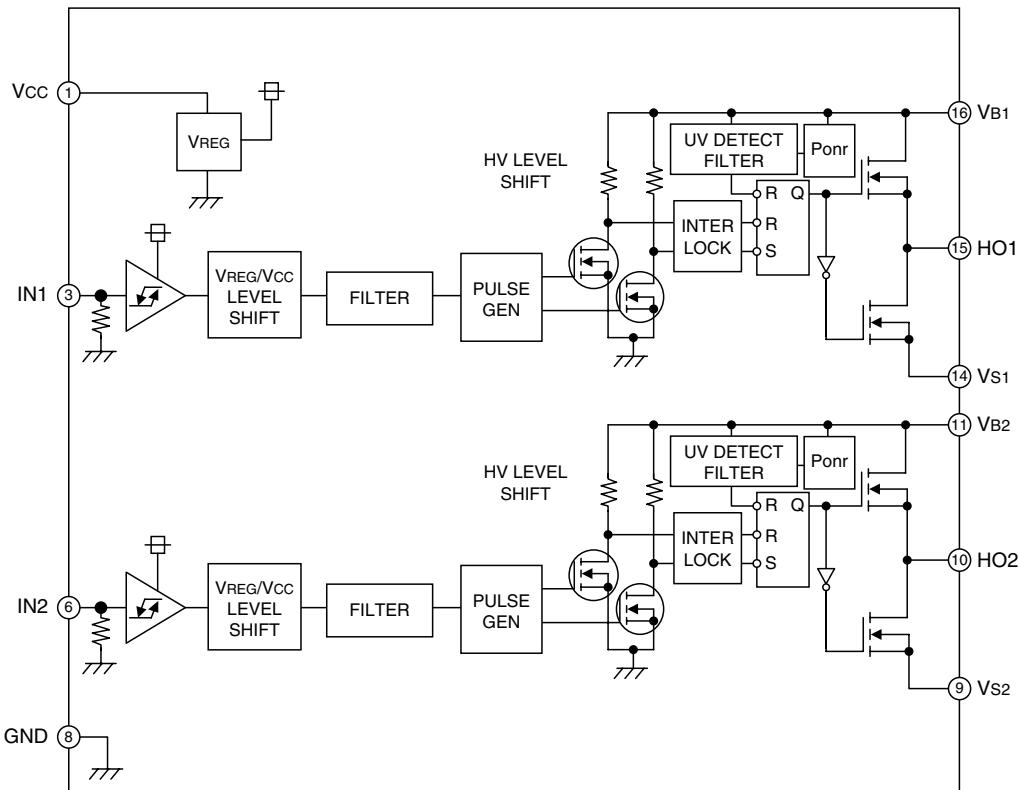
**APPLICATIONS**

MOSFET and IGBT module inverter driver for PDP, HID lamp, refrigerator, air-conditioner, washing machine, AC-servomotor and general purpose.

**PIN CONFIGURATION (TOP VIEW)**

NC: NO CONNECTION

Outline:16P2N

**BLOCK DIAGRAM**

## HIGH VOLTAGE HALF BRIDGE DRIVER

## ABSOLUTE MAXIMUM RATINGS (Ta = 25°C unless otherwise specified)

Symbol	Parameter	Test conditions	Ratings	Unit
V <sub>B</sub>	High Side Floating Supply Absolute Voltage	V <sub>B1</sub> or V <sub>B2</sub>	-0.5 ~ 624	V
V <sub>S</sub>	High Side Floating Supply Offset Voltage	V <sub>S1</sub> or V <sub>S2</sub>	V <sub>B</sub> -24 ~ V <sub>B</sub> +0.5	V
V <sub>BS</sub>	High Side Floating Supply Voltage	V <sub>BS1</sub> = V <sub>B1</sub> -V <sub>S1</sub> or V <sub>BS2</sub> = V <sub>B2</sub> -V <sub>S2</sub>	-0.5 ~ 24	V
V <sub>OUT</sub>	Output Voltage	H <sub>O1</sub> or H <sub>O2</sub>	V <sub>S</sub> -0.5 ~ V <sub>B</sub> +0.5	V
V <sub>CC</sub>	Low Side Fixed Supply Voltage		-0.5 ~ 24	V
V <sub>IN</sub>	Logic Input Voltage	I <sub>N1</sub> or I <sub>N2</sub>	-0.5 ~ V <sub>CC</sub> +0.5	V
P <sub>D</sub>	Package Power Dissipation	T <sub>a</sub> = 25°C, On Board	1.0	W
K <sub>θ</sub>	Linear Derating Factor	T <sub>a</sub> > 25°C, On Board	8.0	mW/°C
R <sub>th(j-c)</sub>	Junction-Case Thermal Resistance		50	°C/W
T <sub>j</sub>	Junction Temperature		-20 ~ 150*	°C
T <sub>opr</sub>	Operation Temperature		-20 ~ 125	°C
T <sub>stg</sub>	Storage Temperature		-40 ~ 150	°C
T <sub>L</sub>	Solder heat-proof (reflow)	Pb Free	255:10s,max 260	°C

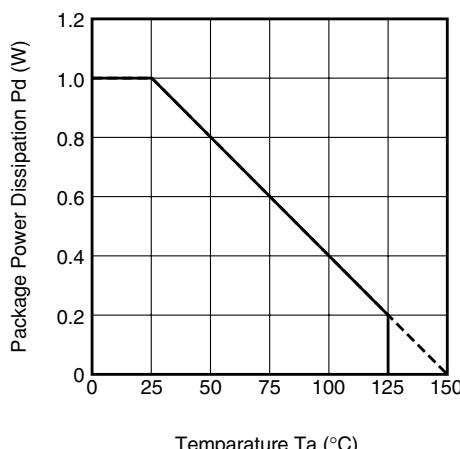
\* Please adjust the V<sub>S</sub> potential to 500V or less when the junction temperature (T<sub>j</sub>) exceeds 125°C.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V <sub>B</sub>	High Side Floating Supply Absolute Voltage	V <sub>B1</sub> or V <sub>B2</sub>	V <sub>S</sub> +10	—	V <sub>S</sub> +20	V
V <sub>S</sub>	High Side Floating Supply Offset Voltage	V <sub>S1</sub> (V <sub>B1</sub> >10V) or V <sub>S2</sub> (V <sub>B2</sub> >10V)	-5	—	500	V
V <sub>BS</sub>	High Side Floating Supply Voltage	V <sub>BS1</sub> = V <sub>B1</sub> -V <sub>S1</sub> or V <sub>BS2</sub> = V <sub>B2</sub> -V <sub>S2</sub>	10	—	20	V
V <sub>OUT</sub>	High Side Output Voltage	H <sub>O1</sub> or H <sub>O2</sub>	V <sub>S</sub>	—	V <sub>B</sub>	V
V <sub>CC</sub>	Low Side Fixed Supply Voltage		10	—	20	V
V <sub>IN</sub>	Logic Input Voltage	I <sub>N1</sub> or I <sub>N2</sub>	0	—	7	V

\* For proper operation, the device should be used within the recommended conditions.

## THERMAL DERATING FACTOR CHARACTERISTIC (MAXIMUM RATING)

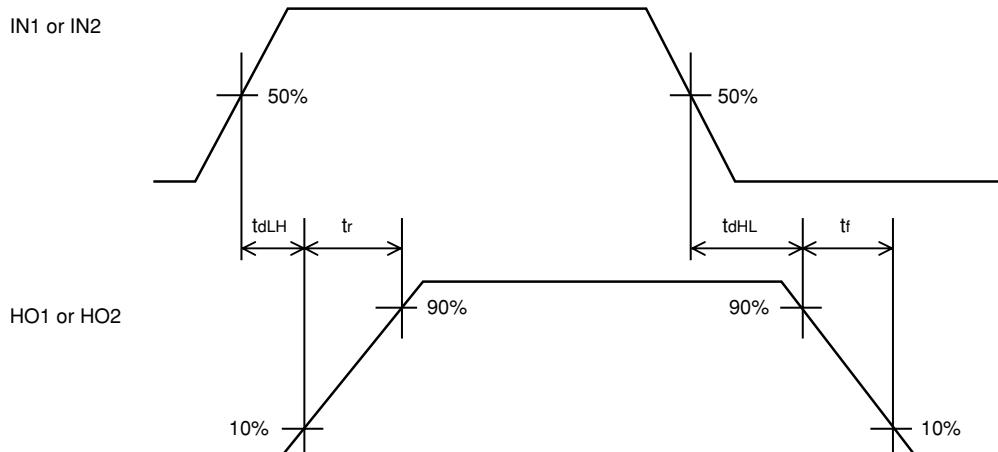


## HIGH VOLTAGE HALF BRIDGE DRIVER

## ELECTRICAL CHARACTERISTICS (Ta = 25°C, Vcc = VBS (= VB-Vs) = 15V, unless otherwise specified)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.*	Max.	
I <sub>FS1</sub>	Floating Supply Leakage Current1	V <sub>B1</sub> = V <sub>S1</sub> = 600V	—	—	1.0	µA
I <sub>FS2</sub>	Floating Supply Leakage Current2	V <sub>B2</sub> = V <sub>S2</sub> = 600V	—	—	1.0	µA
I <sub>BS1</sub>	V <sub>BS1</sub> Standby Current	I <sub>N1</sub> = 0V	—	0.2	0.5	mA
I <sub>BS2</sub>	V <sub>BS2</sub> Standby Current	I <sub>N2</sub> = 0V	—	0.2	0.5	mA
I <sub>CC</sub>	V <sub>CC</sub> Standby Current	I <sub>N1</sub> = I <sub>N2</sub> = 0V	—	0.3	0.6	mA
V <sub>OH</sub>	High Level Output Voltage	I <sub>O</sub> = 0A, H <sub>O1</sub> , H <sub>O2</sub>	13.8	14.4	—	V
V <sub>OL</sub>	Low Level Output Voltage	I <sub>O</sub> = 0A, H <sub>O1</sub> , H <sub>O2</sub>	—	—	0.1	V
V <sub>IH</sub>	High Level Input Threshold Voltage	I <sub>N1</sub> , I <sub>N2</sub>	4.0	—	—	V
V <sub>IL</sub>	Low Level Input Threshold Voltage	I <sub>N1</sub> , I <sub>N2</sub>	—	—	0.8	V
I <sub>IH</sub>	High Level Input Bias Current	V <sub>IN</sub> = 5V, I <sub>N1</sub> , I <sub>N2</sub>	—	17	40	µA
I <sub>IL</sub>	Low Level Input Bias Current	V <sub>IN</sub> = 0V, I <sub>N1</sub> , I <sub>N2</sub>	—	—	2	µA
V <sub>BSUVR</sub>	V <sub>BS</sub> Supply UV Reset Voltage	V <sub>BS1</sub> , V <sub>BS2</sub>	8.0	8.9	9.8	V
V <sub>BSUVH</sub>	V <sub>BS</sub> Supply UV Hysteresis Voltage	V <sub>BS1</sub> , V <sub>BS2</sub>	0.3	0.7	—	V
t <sub>VBSUV</sub>	V <sub>BS</sub> Supply UV Filter Time	V <sub>BS1</sub> , V <sub>BS2</sub>	—	7.5	—	µs
V <sub>PONR</sub>	Power-On Reset Voltage	V <sub>BS1</sub> , V <sub>BS2</sub>	—	—	6.0	V
t <sub>PONR(FIL)</sub>	Power-On Reset Filter Tlme	V <sub>BS1</sub> , V <sub>BS2</sub>	300	—	—	ns
I <sub>OH</sub>	Output High Level Short Circuit Pulsed Current	V <sub>O</sub> = 0V, V <sub>IN</sub> = 5V, PWD < 10µs, H <sub>O1</sub> , H <sub>O2</sub>	2.0	3.0	—	A
I <sub>OL</sub>	Output Low Level Short Circuit Pulsed Current	V <sub>O</sub> = 15V, V <sub>IN</sub> = 0V, PWD < 10µs, H <sub>O1</sub> , H <sub>O2</sub>	2.0	3.0	—	A
R <sub>OH</sub>	Output High Level On Resistance	I <sub>O</sub> = -200mA, R <sub>OH</sub> = (V <sub>OH</sub> -V <sub>O</sub> ) / I <sub>O</sub> H <sub>O1</sub> , H <sub>O2</sub>	—	10	20	Ω
R <sub>OL</sub>	Output Low Level On Resistance	I <sub>O</sub> = 200mA, R <sub>OL</sub> = V <sub>O</sub> / I <sub>O</sub> H <sub>O1</sub> , H <sub>O2</sub>	—	2.5	3.0	Ω
t <sub>dLH</sub>	Turn-On Propagation Delay	CL = 1000pF between H <sub>O1</sub> -V <sub>S1</sub> or H <sub>O2</sub> -V <sub>S2</sub>	—	200	280	ns
t <sub>dHL</sub>	Turn-Off Propagation Delay	CL = 1000pF between H <sub>O1</sub> -V <sub>S1</sub> or H <sub>O2</sub> -V <sub>S2</sub>	—	170	260	ns
t <sub>r</sub>	Turn-On Rise Time	CL = 1000pF between H <sub>O1</sub> -V <sub>S1</sub> or H <sub>O2</sub> -V <sub>S2</sub>	—	25	45	ns
t <sub>f</sub>	Turn-Off Fall Time	CL = 1000pF between H <sub>O1</sub> -V <sub>S1</sub> or H <sub>O2</sub> -V <sub>S2</sub>	—	20	35	ns
Δt <sub>dLH</sub>	Delay Matching, High Side and Low Side Turn-On	t <sub>dLH</sub> (H <sub>O1</sub> ) - t <sub>dLH</sub> (H <sub>O2</sub> )	—	—	30	ns
Δt <sub>dHL</sub>	Delay Matching, High Side and Low Side Turn-Off	t <sub>dHL</sub> (H <sub>O1</sub> ) - t <sub>dHL</sub> (H <sub>O2</sub> )	—	—	30	ns
IN(FIL)	Input Filter Time	CONVEX PULSE : I <sub>N1</sub> , I <sub>N2</sub>	—	90	—	ns
		CONCAVE PULSE : I <sub>N1</sub> , I <sub>N2</sub>	—	90	—	ns

\* Typ. is not specified.

**HIGH VOLTAGE HALF BRIDGE DRIVER****TIMING REQUIREMENT****FUNCTION TABLE**

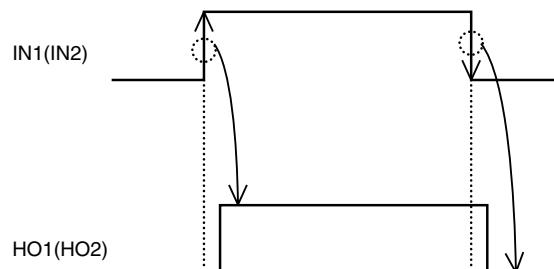
IN1	IN2	VBS1 UV	VBS2 UV	HO1	HO2	Behavioral state
H→L	H→L	H	H	L	L	HO1=HO2=Low
H→L	L→H	H	H	L	H	HO2=High
L→H	H→L	H	H	H	L	HO1=High
L→H	L→H	H	H	H	H	HO1=HO2=High
X	H→L	L	H	L	L	HO1=Low, VBS1 UV tripped
X	L→H	L	H	L	H	HO2=High, VBS1 UV tripped
H→L	X	H	L	L	L	HO2=Low, VBS2 UV tripped
L→H	X	H	L	H	L	HO1=High, VBS2 UV tripped

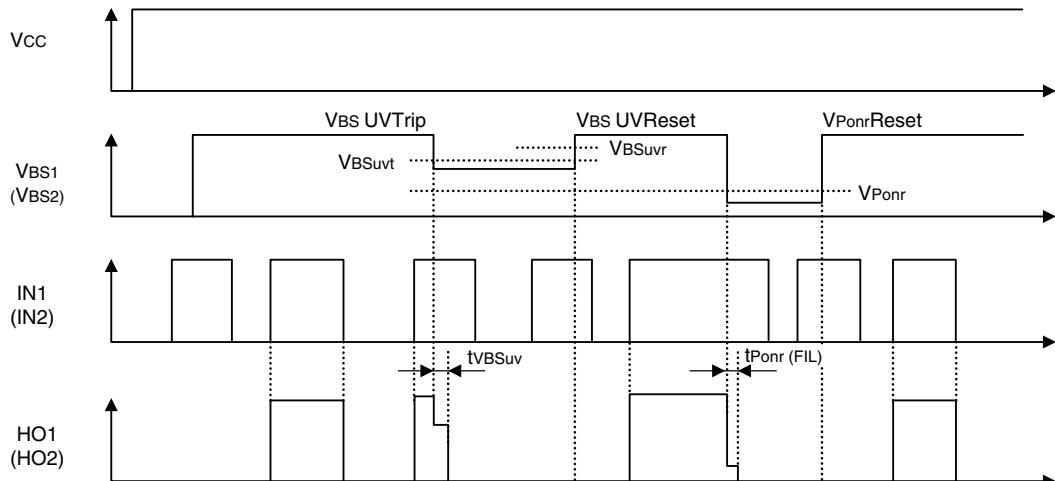
Note1 : "L" state of VBS1 UV, VBS2 UV means that UV trip voltage.

When input signal(IN1 and IN2) is "H" at the same time, then output signal (Both HO1 and HO2) is "H".

2 : X : L→H or H→L.

3 : Output signal (HO1, HO2) is triggered by the edge of input signal.



**HIGH VOLTAGE HALF BRIDGE DRIVER****TIMING DIAGRAM****1. Input/Output Timing**

HIGH ACTIVE (When input signal is "H", then output signal is "H".)

**2. Vbs Supply Under Voltage Lockout**

If Vbs supply voltage drops below UV trip voltage ( $V_{BSUVT}$ ) for Vbs supply UV filter time, output signal is shut down. As soon as Vbs supply voltage rises over UV reset voltage, output signal HO becomes "H" at following "H" edge of input signal.

Note: If the Vbs drops below VPON, the filter time will become tPOR (FIL) instead of tVBSUV.

**3. Allowable Supply Voltage Transient**

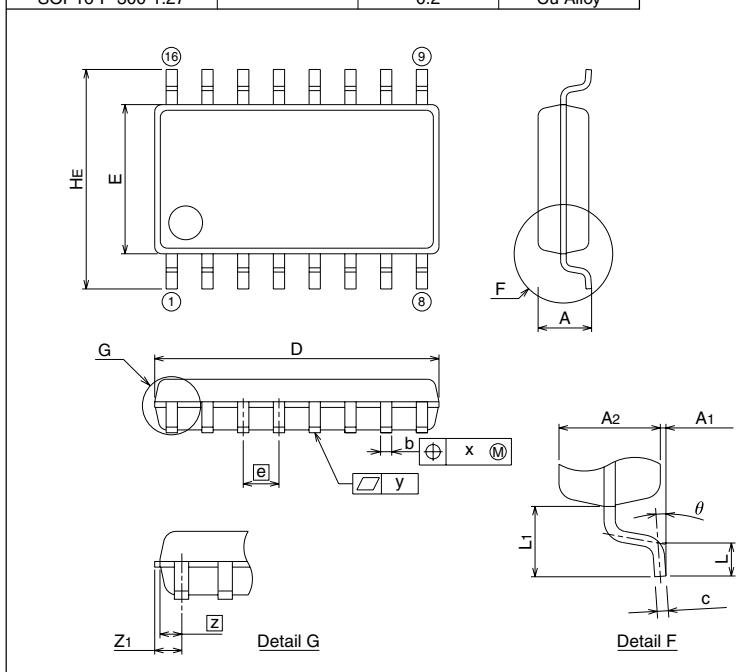
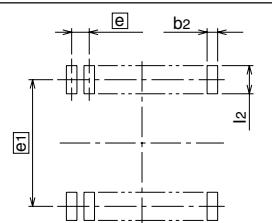
It is recommended to supply Vcc firstly and supply Vbs1(Vbs2) secondly. When shutting off supply voltage, please shut off Vbs1(Vbs2) firstly and shut off Vcc secondly. When applying Vcc and Vbs1(Vbs2), power supply should be applied slowly. If it rises rapidly, output signal (HO or LO) may be malfunction.

Note: If Vcc is below its recommended value: 10V, output may not response input signals.

Please take enough evaluation in the case of power supply shut down and power supply applying after its shut-down.

**HIGH VOLTAGE HALF BRIDGE DRIVER****PACKAGE OUTLINE****16P2N-A**

EIAJ Package Code SOP16-P-300-1.27	JEDEC Code JESD27-100	Weight(g) 0.2	Lead Material Cu Alloy
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**Plastic 16pin 300mil SOP****Recommended Mount Pad**

Symbol	Dimension in Millimeters		
	Min	Nom	Max
A			2.1
A <sub>1</sub>	0	0.1	0.2
A <sub>2</sub>			1.8
b	0.35	0.4	0.5
c	0.18	0.2	0.25
D	10.0	10.1	10.2
E	5.2	5.3	5.4
[e]		1.27	
h <sub>E</sub>	7.5	7.8	8.1
L	0.4	0.6	0.8
L <sub>1</sub>			1.25
[Z]		0.605	
Z <sub>1</sub>			0.755
x			0.25
y			0.1
$\theta$	0°		8°
b <sub>2</sub>		0.76	
[e1]		7.62	
l <sub>2</sub>	1.27		

Aug. 2009